

GSM6320XF

60V N-Channel MOSFET

Product Description

The N-Channel enhancement mode power field effect transistor is using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

The device is well suited for high efficiency fast switching applications.

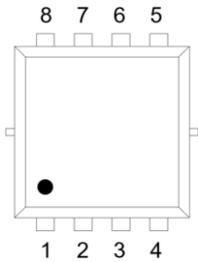
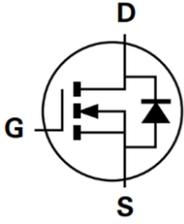
Features

- $R_{DS(ON)} = 2.3m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} = 3.4m\Omega @ V_{GS}=4.5V$
- DFN5X6-8L Package
- RoHS Compliant and Halogen Free

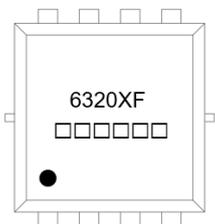
Applications

- MB / VGA / Vcore
- POL Applications
- SMPS

Packages & Pin Assignments

DFN5X6-8L			Equivalent Circuit		
					
Pin	Symbol	Description	Pin	Symbol	Description
1	S	Source	8	D	Drain
2	S	Source	7	D	Drain
3	S	Source	6	D	Drain
4	G	Gate	5	D	Drain

Ordering and Marking Information

Ordering Information			
Part Number	Package	Part Marking	Quantity / Reel
GSM6320XF	DFN5X6-8L	6320XF □□□□□□	3,000 PCS
GSM6320 1 2			
- Product Code: GSM6320		- Package Code: 1 is X for DFN5X6-8L	
		- Green Level: 2 is F for RoHS Compliant and Halogen Free	
Marking Information			
		- Product Code: 6320XF	
		- GS Code: □□□□□□	
		● Dot denotes Pin 1	

Absolute Maximum Ratings (T_A = 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit
V _{DSS}	Drain-Source Voltage	60	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current (Silicon Limited)	T _C =25°C	164
		T _C =100°C	104
	Continuous Drain Current (Package Limited)		100
I _{DM}	Pulsed Drain Current ¹	320	A
I _{AS}	Single Pulse Avalanche Current, L = 0.1mH ¹	44	A
E _{AS}	Single Pulse Avalanche Energy, L = 0.1mH ¹	165	mJ
P _D	Power Dissipation	T _C =25°C	125
		T _C =100°C	50
R _{θJC}	Thermal Resistance-Junction to Case	1	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient ²	62	°C/W
T _J	Operating Junction Temperature Range	-55 to +150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C

NOTE:

- Single pulse width is limited by max junction temperature.
- The device mounted on 1in² FR-4 board with 2oz. Copper

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
B _V DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	-	-	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
I _{GSS}	Gate-Source Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.2	-	2.5	V
R _{DS(ON)}	Drain-Source On-Resistance	V _{GS} =10V, I _D =50A	-	1.9	2.3	mΩ
		V _{GS} =4.5V, I _D =20A	-	2.8	3.4	
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =20A	-	55	-	S
Dynamic Characteristics						
R _g	Gate Resistance	f=1MHz		0.9		Ω
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	-	4947	-	pF
C _{oss}	Output Capacitance		-	2850	-	
C _{rss}	Reverse Transfer Capacitance		-	26	-	
Q _g	Total Gate Charge	V _{DS} =30V, I _D =50A V _{GS} =10V	-	98	-	nC
Q _{gs}	Gate-Source Charge		-	18	-	
Q _{gd}	Gate-Drain Charge		-	24	-	
t _{d(on)}	Turn-On Delay Time	V _{DD} =30V, I _D =50A V _{GS} =10V, R _g =3Ω	-	19	-	ns
t _r	Turn-On Rise Time		-	12	-	
t _{d(off)}	Turn-Off Delay Time		-	42	-	
t _f	Turn-Off Fall Time		-	30	-	
Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =1A	-	-	1	V
t _{rr}	Reverse Recovery Time	I _F =50A, dI/dt=100A/μs	-	88	-	ns
Q _{rr}	Reverse Recovery Charge		-	175	-	nC

Typical Performance Characteristics

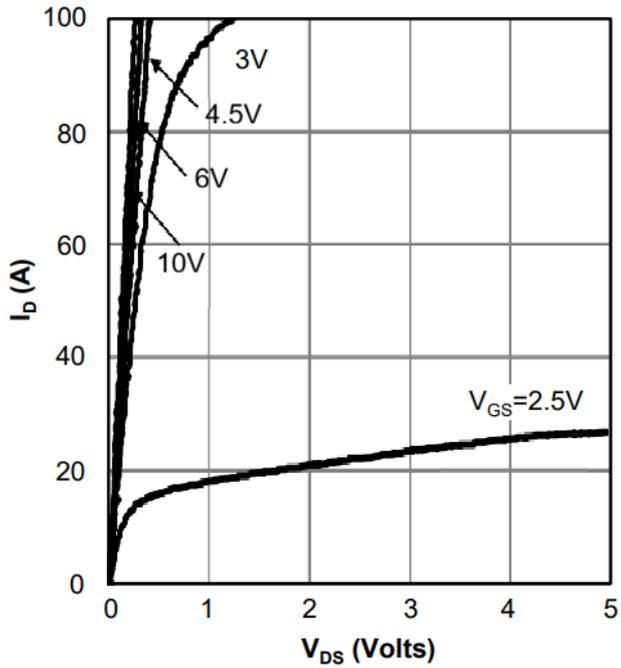


FIG.1 Output Characteristics

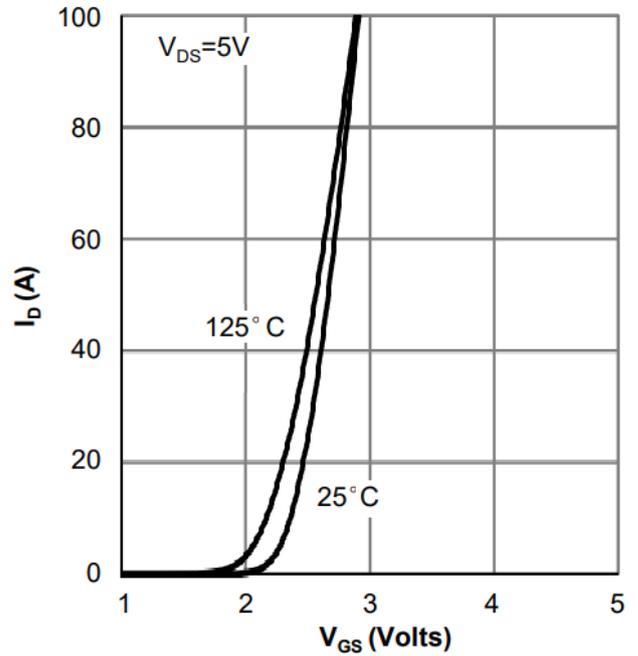


FIG.2 Transfer Characteristics

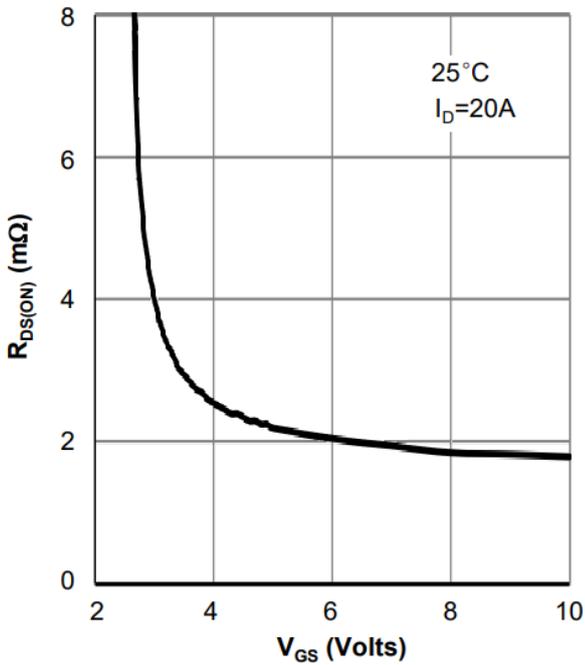


FIG.3 On-Resistance vs. Gate Voltage

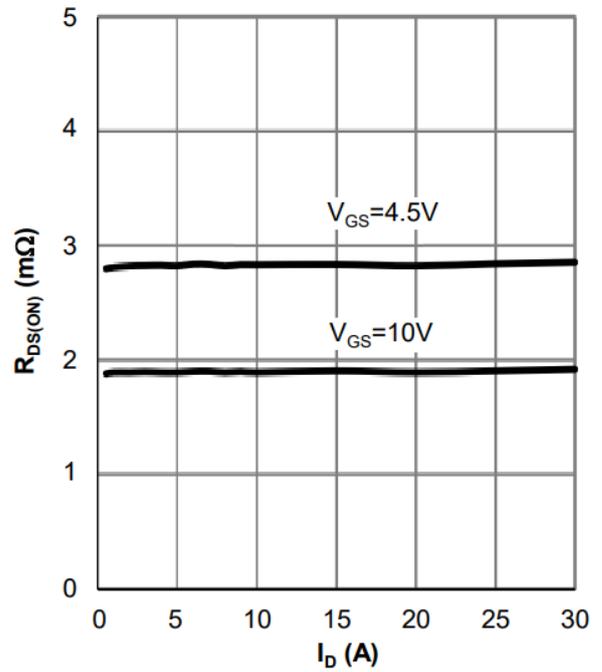


FIG.4 On-Resistance vs. Drain Current

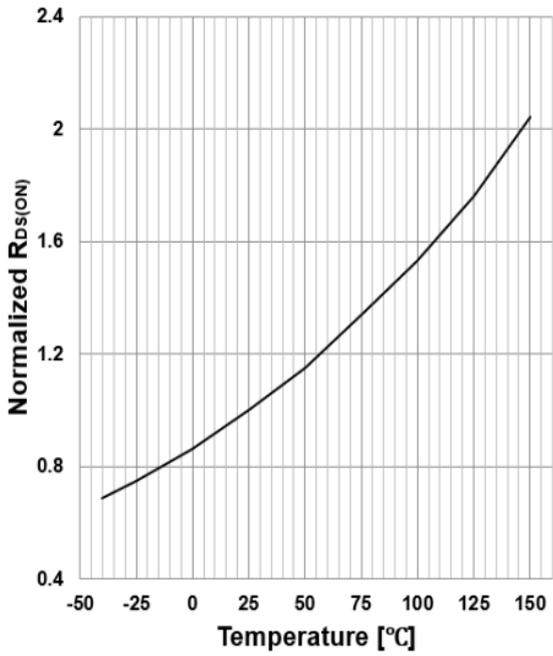


FIG.5 Normalized On-Resistance vs. T_J

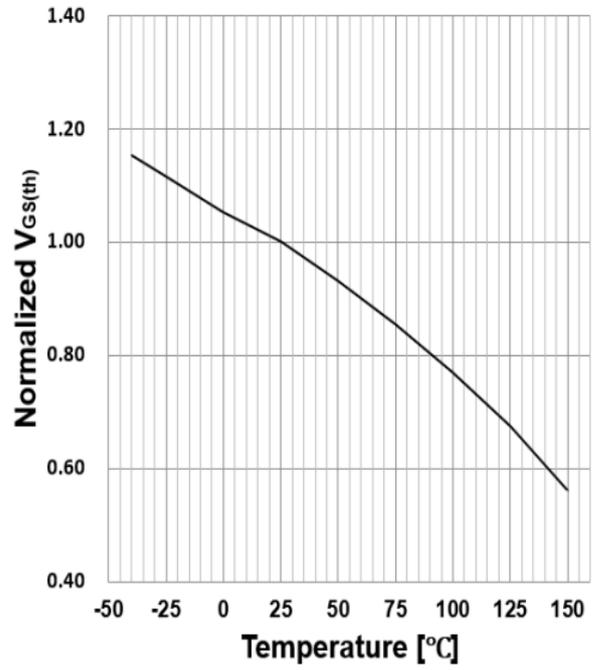


FIG.6 Normalized $V_{GS(th)}$ vs. T_J

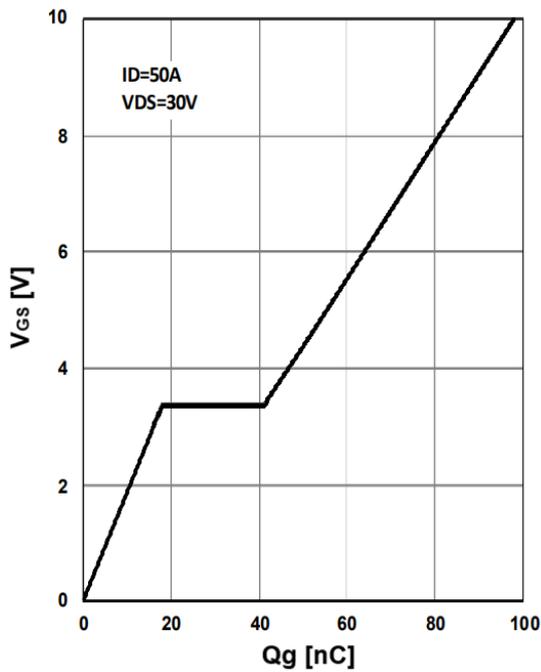


FIG.7 Gate Charge Characteristics

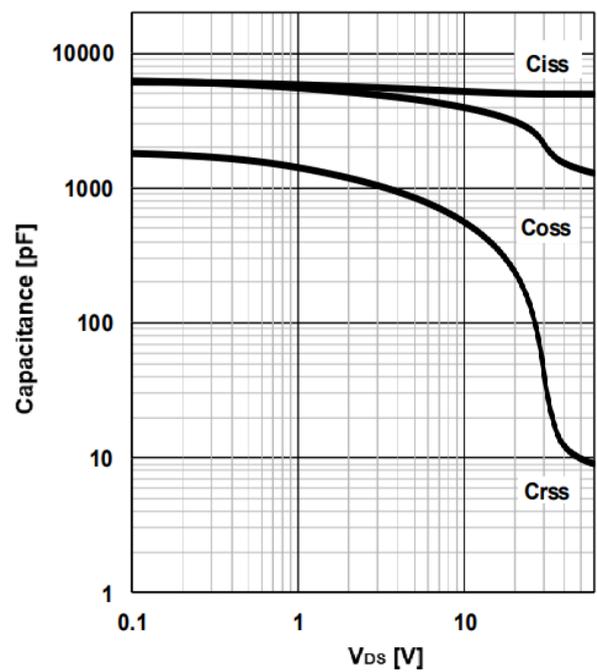


FIG.8 Capacitance Characteristics

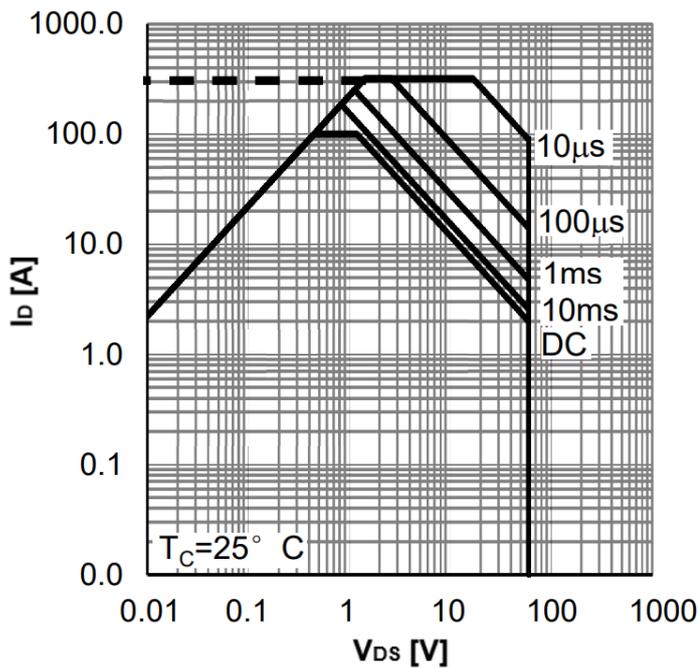


FIG.9 Maximum Safe Operation Area

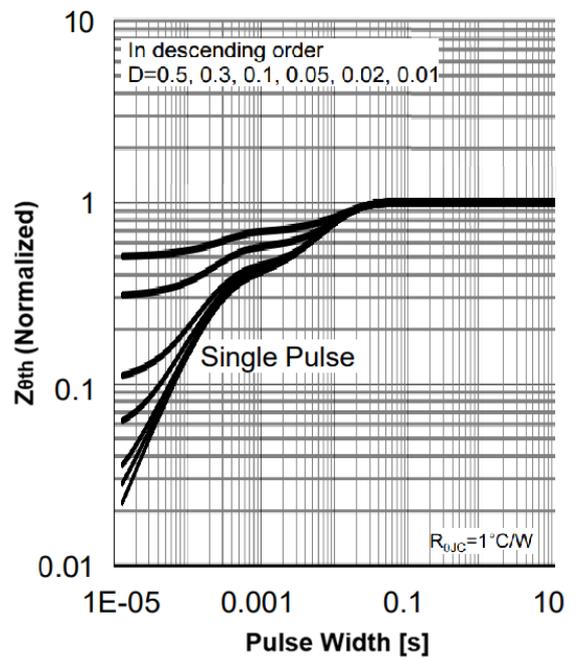


FIG.10 Transient Thermal Impedance (Normalized)

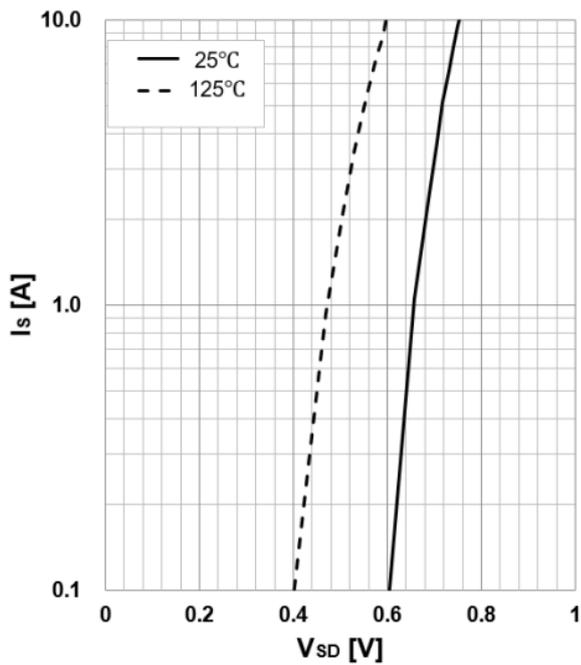
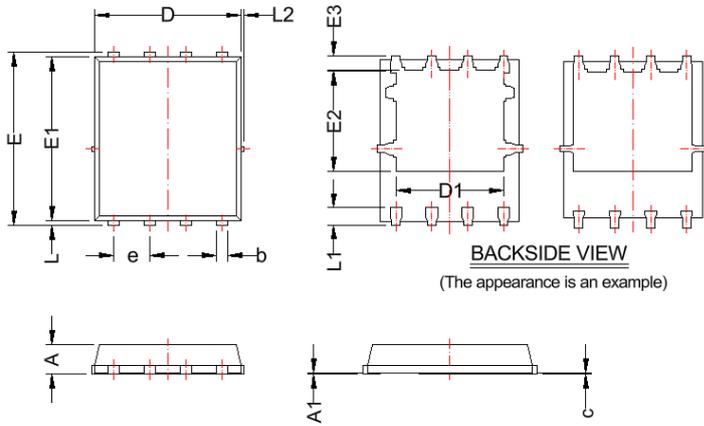


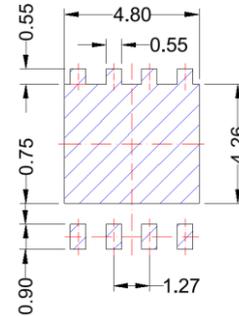
FIG.11 Body-Diode Characteristics

DFN5X6-8L

Package Dimension



Recommended Land Pattern



Unit: mm

Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.80	1.20	0.031	0.047
A1	0.00	0.05	0.000	0.002
b	0.25	0.51	0.010	0.020
c	0.20	0.35	0.008	0.014
D	4.80	5.40	0.189	0.213
D1	3.40	4.60	0.134	0.181
E	5.90	6.20	0.232	0.244
E1	5.40	5.90	0.213	0.232
E2	3.20	3.80	0.126	0.150
E3	0.40	0.80	0.016	0.031
e	1.27 BSC		0.050 BSC	
L	0.06	0.25	0.002	0.010
L1	0.34	0.75	0.013	0.030
L2	---	0.15	---	0.006

NOTE:

Dimensions are exclusive of Burrs, Mold Flash and Tie Bar extrusions.

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